

**BTX18-100/BTX18-200/BTX18-300
 BTX18-400/BTX18-500**

Anode to Cathode - Ratings

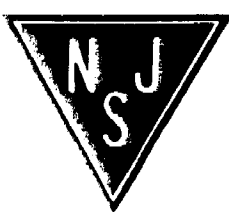
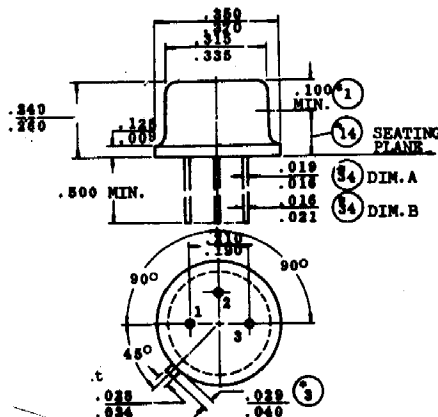
Voltage ¹⁾

SILICON THYRISTORS

Symbol	Ratings	BTX18-100	BTX18-200	BTX18-300	BTX18-400	BTX18-500	
V _R	Continuous Reverse Voltage	100	200	300	400	500	V
V _{RWM}	Crest Working Reverse Voltage	100	200	300	400	500	V
V _{RRM}	Repetitive Peak Reverse Voltage ($\delta = 0.01$; f=50Hz)	120	240	350	500	600	V
V _{RSM}	Non-repetitive peak reverse voltage (t<10ms)	120	240	350	500	600	V
V _{DWM}	Crest Working off-state Voltage	100	200	300	400	500	V
V _D	Continuous off-state Voltage	100	200	300	400	500	V
V _{DRM}	Repetitive peak off-state voltage ($\delta = 0.01$; f=50Hz)	120	240	350	500	600	V ²⁾
V _{DSM}	Non-repetitive peak off-state voltage (t<10ms)	120	240	350	500	600	V ²⁾

Currents

Symbol	Ratings	BTX18-100	BTX18-200	BTX18-300	BTX18-400	BTX18-500	
I _{T(AV)}	Average on-state current (averaged over any 20 ms period)	T _{CASE} =105°C		Max : 1.0			A
		T _{AMB} =60°C, in free air		Max : 250			mA
I _T	On-state Current (D.C.) T _{CASE} =100°C			Max : 1.6			A
I _{T(RMS)}	RMS on-state Current			Max : 1.6			A



Symbol	Ratings	BTX18-	BTX18-	BTX18-	BTX18-	BTX18-	
		100	200	300	400	500	
I_{TRM}	Repetitive Peak on-state Current	Max : 10					A
I_{TSM}	Non-repetitive peak on-state current $t=10ms$; $T_j=125^\circ C$ prior to surge	10 A					V
T_j T_{stg}	Junction Temperature Storage Temperature	Max : $125^\circ C$ -55 to $+125^\circ C$					$^\circ C$

- 1) These ratings apply for zero or negative bias on the gate with respect to the cathode, and when a resistor $R < 1\text{ k}\Omega$ is connected between gate and cathode
- 2) The device is not suitable for operation in the forward breakover mode.

Gate to Cathode - Ratings

With 1Ω resistor between gate and cathode

Symbol	Ratings	BTX18	BTX18	BTX18	BTX18	BTX18	
		-100	-200	-300	-400	-500	
V_{FGM}	Forward Peak Voltage	Max : 10 V					V
V_{RGM}	Reverse Peak Voltage	Max : 5 V					V
I_{FGM}	Forward Peak Current	Max : 0.2					A
$P_{G(AV)}$	Average Power Dissipation (averaged over any 20 ms period)	Max : 0.05					W
P_{GM}	Peak Power Dissipation	Max : 0.5					W

Temperatures

Symbol	Ratings	BTX18	BTX18	BTX18	BTX18	BTX18	
		-100	-200	-300	-400	-500	
$R_{th\ j-c}$	From Junction to Case	10					$^\circ C/W$
$R_{th\ j-a}$	From Junction to Ambient	200					$^\circ C/W$
$Z_{th\ j-c}$	Transient Thermal Resistance ($t=10\text{ ms}$)	2.5					$^\circ C/W$

Anode to Cathode - Characteristics

Symbol	Ratings	BTX18	BTX18	BTX18	BTX18	BTX18	
		-100	-200	-300	-400	-500	
V_T	On State Voltage $I_T=1.0\text{ A}$, $T_j=25^\circ C$	< 1.5	< 1.5	< 1.5	< 1.5	< 1.5	$V^1)$

Symbol	Ratings		BTX18 -100	BTX18 -200	BTX18 -300	BTX18 -400	BTX18 -500	
I_{RM}	Peak Reverse Current $V_{RM}=V_{RWmax}$; $T_j=125^\circ C$	<	800	400	275	200	160	μA
I_{DM}	Peak off-state Current $V_{DM}=V_{DWMmax}$; $T_j=125^\circ C$	<	800	400	275	200	160	μA
I_L	Latching current, $T_j=125^\circ C$		Typ : 10					mA
I_H	Holding Current ; $T_j=25^\circ C$	<	5.0 ²⁾					mA

Gate to Cathode – Characteristics

Symbol	Ratings		BTX18 -100	BTX18 -200	BTX18 -300	BTX18 -400	BTX18 -500	
V_{GT}	Voltage that will trigger all devices $T_j=25^\circ C$	>	2.0					V
V_{GD}	Voltage that will not trigger any device $T_j=125^\circ C$	<	200					mV
I_{GT}	Current that will trigger all devices $T_j=25^\circ C$	>	5.0					mA

Switching Characteristics

Symbol	Ratings		BTX18 -100	BTX18 -200	BTX18 -300	BTX18 -400	BTX18 -500	
Turn off time when switched from $I_T=300$ mA to $I_R=175$ mA	$T_j=25^\circ C$	t_q	Type : 20					μs
	$T_j=125^\circ C$		Typ : 35					
I_{DM}	Peak off-state Current $V_{DM}=V_{DWMmax}$; $T_j=125^\circ C$	<	800	400	275	200	160	μs

- 1) V_T is measured along the leads at 1 cm from the case
- 2) Measured under the following conditions :
 Anode supply voltage = +6.0V
 Initial on-state current after gate triggering = 50mA
 The current is reduced until the device turns off.